Abstract

Method for producing a semiconductor wafer

A method for producing a semiconductor wafer, comprising in the order: (a) simultaneous double-side material-removing of the wafer, which is processed between two rotating ring-shaped working disks containing abrasives having an average grain size of 5.0-20.0 µm; (b) treatment of both sides with an alkaline medium; (c) grinding of both sides, wherein in each case one side is fixedly held by means of a holder, while the other side is processed with a grinding tool containing abrasives having an average grain size of 1.0-10.0 µm, wherein the average grain size is less than the average size of the abrasives of the disks used in (a); (d) polishing of both sides with a pad containing abrasives having an average size of 0.1-1.0 µm; (e) polishing of the front side with a stock removal pad containing no abrasives, with the supply of an agent containing abrasives; (f) CMP of the front side.